45V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN D-PAK

SUMMARY

 $\mbox{BV}_{\mbox{CEO}}$ = 45V : $\mbox{R}_{\mbox{SAT}}$ = 77m $\Omega;$ $\mbox{I}_{\mbox{C}}$ = 3A

DESCRIPTION

Packaged in the D-Pak outline this high gain 45V NPN transistor offers low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.



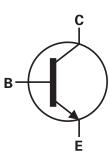
DPAK

FEATURES

- 3 Amps continuous current
- Up to 6 Amps peak current
- Low saturation voltages
- High gain

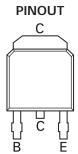
APPLICATIONS

- DC DC Converters
- MOSFET gate drivers
- · Charging circuits
- Power switches
- Siren drivers



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXT690BKTC	13"	16mm embossed	2500 units



DEVICE MARKING

ZXT690B



ABSOLUTE MAXIMUM RATINGS

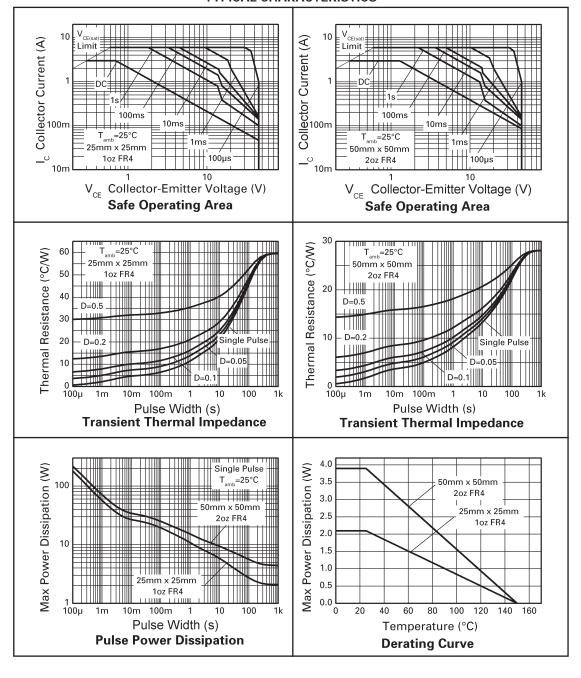
PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	BV _{CBO}	60	V
Collector-Emitter Voltage	BV _{CEO}	45	V
Emitter-Base Voltage	BV _{EBO}	5	V
Continuous Collector Current	I _C	3	Α
Peak Pulse Current	I _{CM}	6	Α
Base Current	I _B	0.5	Α
Power Dissipation at T _A =25°C ^(a)	P _D	2.1	W
Linear Derating Factor		16.8	mW/°C
Thermal Resistance Junction to Ambient		59	°C/W
Power Dissipation at T _A =25°C ^(b)	P _D	3.0	W
Linear Derating Factor		24.4	mW/°C
Thermal Resistance Junction to Ambient		41	°C/W
Power Dissipation at T _A =25°C (c)	P _D	3.9	W
Linear Derating Factor		30.9	mW/°C
Thermal Resistance Junction to Ambient		32	°C/W
Operating and Storage Temperature Range	T _j , T _{stg}	-55 to +150	°C

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) For a device surface mounted on 50mm x 50mm FR4 PCB with high coverage of single sided 1oz copper in still air conditions.
- (c) For a device surface mounted on 50mm x 50mm FR4 PCB with high coverage of single sided 2oz copper in still air conditions.



TYPICAL CHARACTERISTICS





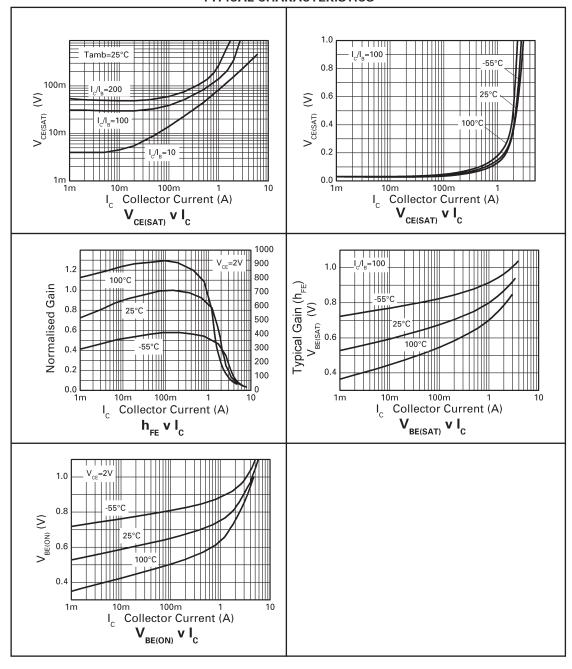
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25$ °C unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-Base Breakdown Voltage	BV _{CBO}	60	145		V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	45	65		V	I _C = 10mA ⁽¹⁾
Emitter-Base Breakdown Voltage	BV _{EBO}	5	8.2		V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}		<1	20	nA	V _{CB} = 35V
Collector Cut-Off Current	I _{CES}		<1	20	nA	V _{CB} = 35V
Emitter Cut-Off Current	I _{EBO}		<1	20	nA	V _{EB} = 4V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		50	85	mV	$I_C = 0.1A, I_B = 0.5 \text{mA}^{(1)}$
			240	360	mV	$I_C = 1A, I_B = 5mA^{(1)}$
			210	320	mV	$I_C = 2A$, $I_B = 40mA^{(1)}$
			230	350	mV	I _C = 3A, I _B = 150mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}		1.0	1.2	mV	$I_C = 3A, I_B = 150 \text{mA}^{(1)}$
Base-Emitter Turn-On Voltage	V _{BE(ON)}		0.9	1.1	mV	$I_C = 3A, V_{CE} = 2V^{(1)}$
Static Forward Current Transfer Ratio	h _{FE}	500				$I_C = 100 \text{mA}, V_{CE} = 2V^{(1)}$
		400				$I_C = 1A, V_{CE} = 2V^{(1)}$
		150				$I_C = 2A, V_{CE} = 2V^{(1)}$
		60				$I_C = 3A, V_{CE} = 2V^{(1)}$
Transition Frequency	f _T	150			MHz	I _C = 50mA, V _{CE} = 5V
						f = 50MHz
Output Capacitance	СОВО		16		pF	V _{CB} = 10V, f = 1MHz ⁽¹⁾
Switching Times	t _{ON}		33		ns	$I_C = 500 \text{mA}, V_{CC} = 10 \text{V},$
	t _{OFF}		1300		ns	$I_{B1} = I_{B2} = 50 \text{mA}$

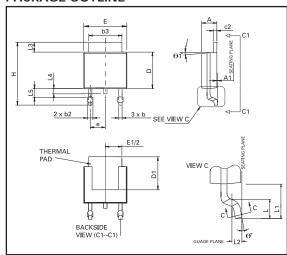


NOTES (1) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS



PACKAGE OUTLINE



Controlling dimensions are in millimetres. Approximate conversions are given in inches

DIM	MILLIMETRES		INCHES		
	MIN	MAX	MIN	MAX	
Α	2.18	2.38	0.086	0.094	
A1	_	0.127	_	0.005	
b	0.635	0.89	0.025	0.035	
b2	0.762	1.114	0.030	0.045	
b3	5.20	5.46	0.205	0.215	
С	0.457	0.609	0.018	0.024	
c2	0.457	0.584	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	5.20	_	0.205	_	
E	6.35	6.73	0.250	0.265	
E1	4.32	_	0.170	_	
е	2.30 BSC		0.090 BSC		
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74	REF	0.108 REF		
L2	0.051 BSC		0.020 BSC		
L3	0.89	1.27	0.035	0.050	
L4	0.635	1.01	0.025	0.040	
L5	1.14	1.52	0.045	0.060	
θ1°	0°	10°	0°	10°	
θ°	0°	15°	0°	15°	

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